HDL and IBIS 4.1 Models in a Functional DDR Memory Interface Analysis

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Project Definition

- Analyze a complete DDR memory interface in one simulation
- Simulation should consider:
 - Overshoot/Undershoot violations
 - Setup and hold timing violations
 - Include pattern dependant crosstalk between address, command, control, and data signals
 - Slew dependant timing calculations



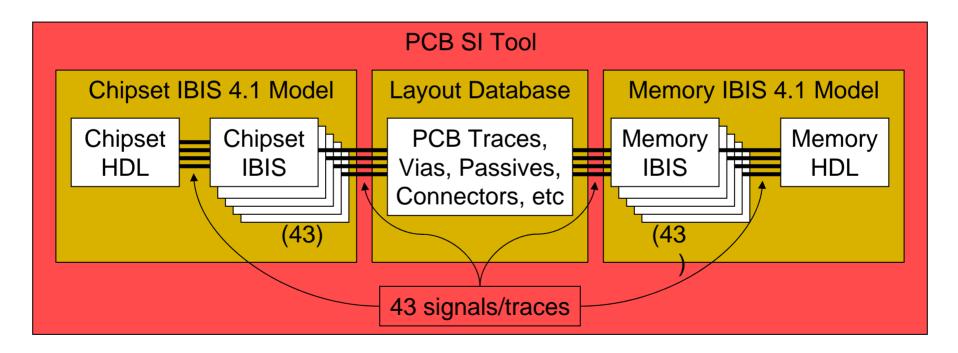
Project Approach

- Combine HDL functional models and IBIS I/O models
- HDL code takes care of timing checks
- IBIS model contains basic electrical checks
- How does it all work?

IBIS 4.1!

Simulation Diagram

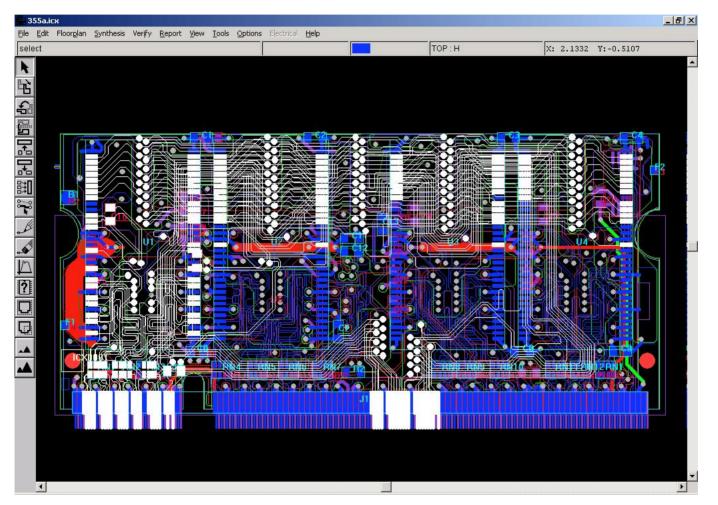
 Connection of HDL functional models and IBIS I/O models to the physical board layout





Analysis Details

• Memory module (simulated traces highlighted in white)





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Analysis Details

- Digital code from the chipset testbench generates the system stimulus
- Random address and data pattern generators ensure realistic stimulus patterns for the Write cycle
- Memory responds to chipset commands, thus automating Read cycle data patterns
- Single simulation completes a Read and Write Cycle multiple cycles can be run to simulate realistic bus utilization



- HDL models contain timing checks
- Timing violations caused by PCB effects are flagged

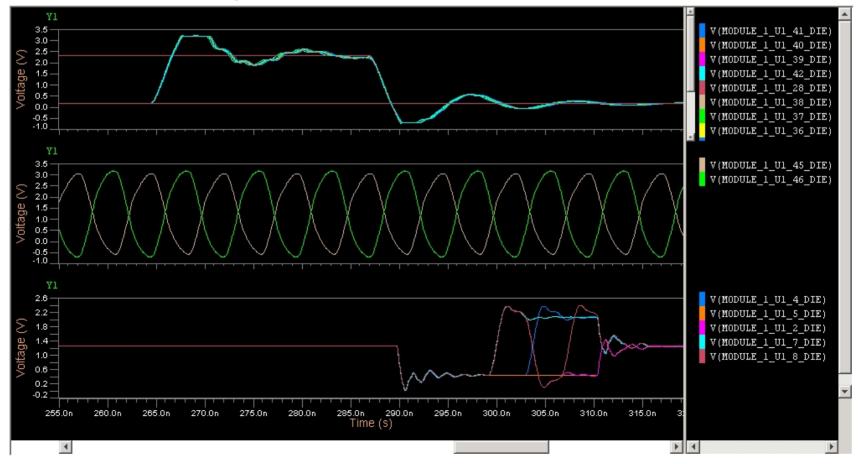
C:\WINDOWS\system32\cmd.exe

Warning:tRP violation during Activate Bank 0 Iteration: 2 in: Y_J1_MT46V64M16_0.STATE_REGISTER Time: 147.849.999 fs MT46V64M16(BEHAVE) Warning:tRFC violation during Activate Iteration: 2 in: Y_J1_MT46V64M16_0.STATE_REGISTER · Time: 147.849.999 fs MT46U64M16(BEHAUE) Warning:RAS# Setup time violation -- tIS 147.849.999 fs Iteration: 2 in: Y_J1_MT46V64M16_0.SETUP_CHECK - MT Time: 46U64M16(BEHAUE) Warning:WE# Setup time violation -- tIS - 147,849,999 fs Iteration: 2 in: Y_J1_MT46V64M16_0.SETUP_CHECK - MT Time: 46U64M16(BEHAVE) Warning:RAS# Hold time violation -- tIH 148,749.999 fs Iteration: 0 in: Y_J1_MT46V64M16_0.HOLD_CHECK - MT4 Time: 6V64M16(BEHAVE) Warning:RAS# Setup time violation -- tIS Iteration: 2 in: Y_J1_MT46V64M16_0.SETUP_CHECK - MT Time: 151.250 ps 46U64M16(BEHAUE) Warning:WE# Setup time violation -- tIS Iteration: 2 in: Y_J1_MT46V64M16_0.SETUP_CHECK - MT Time: 151,250 ps 46U64M16(BEHAUE) Warning:CAS# Hold time violation -- tIH Iteration: 0 in: Y_J1_MT46V64M16_0.HOLD_CHECK - MT4 152.150 ns Time: 6V64M16(BEHAVE) Warning:RAS# Hold time violation -- tIH



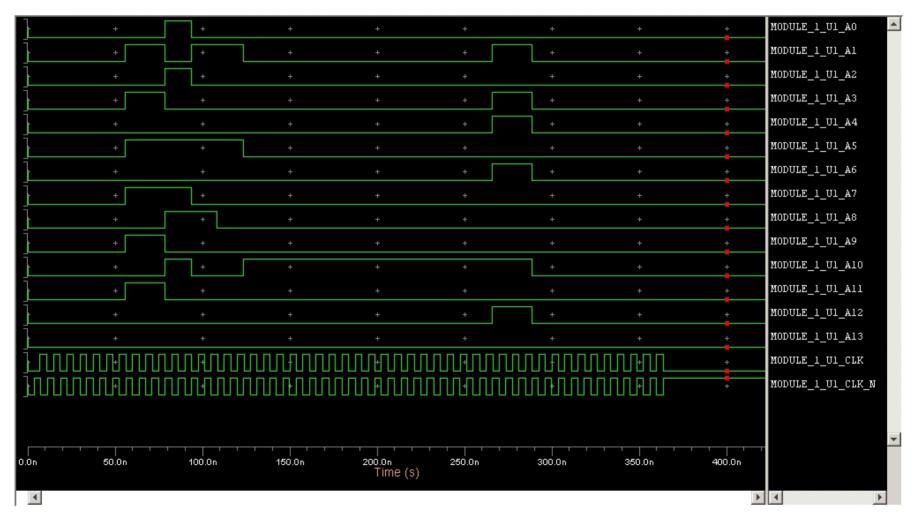
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- Analog Address, Clock, and Data signals at memory during a burst write from the chipset
- Simulation easily changed to generate pseudo-random or fixed address and data patterns



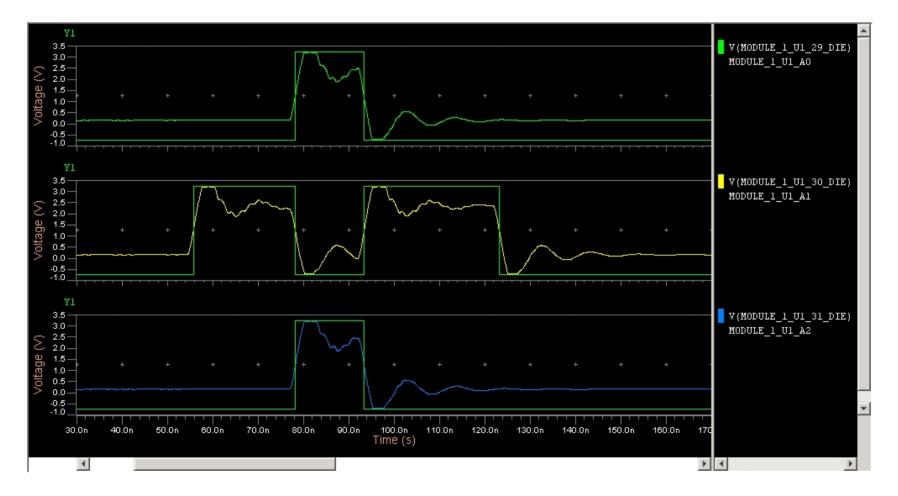
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 Digital Address and Clock signals at the memory die during a burst write from the chipset



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- Combined analog and digital Address signals at the memory die during a burst write from the chipset
- Provides a useful visualization of the logical analog equivalent



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Future Enhancements

- Exercise all 64 DQ signals in the system (instead of 8)
- Use AMS to analyze slew dependant timing outputting results on separate signal
- Model DDR2 system including ODT effects
- Include S-parameter models to replace PCB physical information for enhanced crosstalk analysis
- IBIS enhancements:
 - Instantiating a [Model] in a [Circuit Call] statement
 - Corner-specific Parameters passing



Project Contributors

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